A1 End

the number of P-well plugs required to supply the bias voltage Vbb over a given substrate area.

Please rewrite the paragraph beginning on page 4, last line as follows:

A2 FIG. 5 is an elevation view of FIG. 4 taken at V-V.

Please rewrite the paragraph beginning on page 12, line 9 as follows:

Like the conductive metallic layer described above, if conductive paste 60 is not in direct electrical communication with bonding pad 85, it will still draw unwanted voltage or electrical noise away from substrate 10 to help stabilize the operation of the electrical elements of the device 100. Unwanted voltage noise in substrate 10 may exit the substrate 10 by moving vertically down substrate 10 to conductive paste 60 where it flows through the conductive paste 60. For example, transferred noise in conductive paste 60 may horizontally flow away from gate stacks 40, 42 and re-enter substrate 10 in the proximity of P-well diffusion regions 14. The noise can then flow from P-well diffusion regions 14 to P-well plugs 30. From the P-well plugs 30, the voltage can flow to bonding pads 83, via metalization layers 90, where it can further flow away from active areas of device 100.

A3

Please rewrite the paragraph beginning on page 17, line 13 as follows:

FIG. 5 is an elevation view of FIG. 4 taken at line V-V. Conductive layer 60 is shown attached to the substrate bottom surface 81 with a conductive adhesive 62. Lead fingers 87 are shown attached to the top surface 91 of device 100 by a conductive adhesive compound 94 using well known lead on chip techniques. Also shown is bonding pad 85 which is in electrical communication with conductive layer 60 via wire bond 95.

A4